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AMENDMENTS TO THE CLAIMS:

The following listing of the claims replaces all prior versions, and listings, of the claims in the application:

1. (Currently Amended) A plasma treatment apparatus comprising:
a plurality of plasma generation units comprising a first electrode and a plurality of second electrodes opposed to the first electrode; ~~and~~
a gas supply unit for introducing a process gas into a space between the first electrode and the plurality of second electrodes[.]; ~~and~~
a unit for applying a voltage to a predetermined electrode among the plurality of second electrodes.

wherein the plurality of plasma generation units are arranged linearly in one line or a plurality of lines.

2. (Currently Amended) A plasma treatment apparatus comprising:
a plurality of plasma generation units comprising a first electrode and a plurality of second electrodes opposed to the first electrode; ~~and~~
a gas supply unit for introducing a process gas into a space between the first electrode and the plurality of second electrodes[.]; ~~and~~
a unit for applying a voltage to predetermined electrode among the plurality of second electrodes.

wherein the plurality of plasma generation units are arranged linearly in one line or a plurality of lines; and

wherein at least one of the plurality of second electrodes has a length of equal to or less than 1 mm on a side of an object to be treated.

3. (Currently Amended) A plasma treatment apparatus comprising:
a plurality of plasma generation units comprising a first electrode and a plurality of second electrodes opposed to the first electrode for forming a pattern on an object to be treated; ~~and~~
a gas supply unit for introducing a process gas into a space between the first electrode and the plurality of second electrodes[.]; ~~and~~

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a unit for applying a voltage to a predetermined electrode among the plurality of second electrodes.

wherein the plurality of plasma generation units are arranged linearly in one line or a plurality of lines; and

wherein at least one of the plurality of second electrodes has a length of equal to or less than a square of a line width of the pattern on a side of the object to be treated.

4. (Original) A plasma treatment apparatus according to claim 3, wherein the pattern is a wiring pattern.

5. (Currently Amended) A plasma treatment apparatus according to claim 2[[, wherein]] further comprising a unit for positioning one of the plurality of plasma generation units to the object to be treated ~~or the pattern on the object to be treated is provided.~~

6. (Currently Amended) A plasma treatment apparatus according to claim 3[[, wherein]] further comprising a unit for positioning one of the plurality of plasma generation units to ~~the object to be treated or the pattern on the object to be treated is provided.~~

7. (Currently Amended) A plasma treatment apparatus according to claim 1, ~~further comprising:~~
~~a unit for controlling a voltage applied to a predetermined electrode through a control circuit; and~~
~~a unit for controlling plasma generation on the object to be treated by synchronizing timing of wherein scanning a stage or of the plurality of plasma generation units and timing of applying a is synchronized with the application of the voltage to the predetermined electrode.~~

8. (Currently Amended) A plasma treatment apparatus according to claim 2, ~~further comprising:~~
~~a unit for controlling a voltage applied to a predetermined electrode through a control circuit; and~~
~~a unit for controlling plasma generation on the object to be treated by synchronizing~~

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~~timing of wherein a scanning a stage or of the plurality of plasma generation units and timing of applying a~~ is synchronized with the application of the voltage to the predetermined electrode.

9. (Currently Amended) A plasma treatment apparatus according to claim 3, ~~further comprising:~~

~~a unit for controlling a voltage applied to a predetermined electrode through a control circuit; and~~

~~a unit for controlling plasma generation on the object to be treated by synchronizing timing of wherein a scanning a stage or of the plurality of plasma generation units and timing of applying a~~ is synchronized with the application of the voltage to the predetermined electrode.

10. (Currently Amended) A plasma treatment apparatus according to claim 1, wherein ~~one of the plurality of second electrodes~~ [[is]] are processed by using a focused ion beam apparatus, photolithography, or a laser lithography apparatus.

11. (Currently Amended) A plasma treatment apparatus according to claim 2, wherein ~~one of the plurality of second electrodes~~ [[is]] are processed by using a focused ion beam apparatus, photolithography, or a laser lithography apparatus.

12. (Currently Amended) A plasma treatment apparatus according to claim 3, wherein ~~one of the plurality of second electrodes~~ [[is]] are processed by using a focused ion beam apparatus, photolithography, or a laser lithography apparatus.

13. (Currently Amended) A plasma treatment apparatus according to claim 1, wherein the first electrode and the plurality of second electrodes [[is]] are covered with a dielectric.

14. (Currently Amended) A plasma treatment apparatus according to claim 2, wherein the first electrode and the plurality of second electrodes [[is]] are covered with a dielectric.

15. (Currently Amended) A plasma treatment apparatus according to claim 3, wherein

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the first electrode and the plurality of second electrodes ~~[[is]]~~ are covered with a dielectric.

16. (Currently Amended) A plasma treatment apparatus according to claim 1, wherein the voltage is applied to the predetermined electrode for performing a film formation, the an etching treatment, or the a surface modification over an object to be treated is performed by applying a pulsed electric field into the space between the first electrode and the plurality of second electrodes under atmospheric pressure or under pressure approximate to atmospheric pressure.

17. (Currently Amended) A plasma treatment apparatus according to claim 2, wherein the voltage is applied to the predetermined electrode for performing a film formation, the an etching treatment, or the a surface modification over an object to be treated is performed by applying a pulsed electric field into the space between the first electrode and the plurality of second electrodes under atmospheric pressure or under pressure approximate to atmospheric pressure.

18. (Currently Amended) A plasma treatment apparatus according to claim 3, wherein the forming of the pattern is performed film formation, the etching, or the surface modification is performed by applying a pulsed electric field into the space between the first electrode and the plurality of second electrodes under atmospheric pressure or under pressure approximate to atmospheric pressure.

19. (New) A plasma treatment apparatus according to claim 1 further comprising a stage to which an object to be treated is fixed,
wherein a scanning of the stage is synchronized with the application of he voltage to the predetermined electrode.

20. (New) A plasma treatment apparatus according to claim 2 further comprising a stage to which the object is fixed,
wherein a scanning of the stage is synchronized with the application of the voltage to the predetermined electrode.

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21. (New) A plasma treatment apparatus according to claim 3 further comprising a stage to which the object is fixed,
wherein a scanning of the stage is synchronized with the application of the voltage to the predetermined electrode.

22. (New) A plasma treatment apparatus according to claim 16, wherein the film formation, the etching treatment, or the surface modification is performed under atmospheric pressure or under pressure approximate to atmospheric pressure.

23. (New) A plasma treatment apparatus according to claim 17, wherein the film formation, the etching treatment, or the surface modification is performed under atmospheric pressure or under pressure approximate to atmospheric pressure.